

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

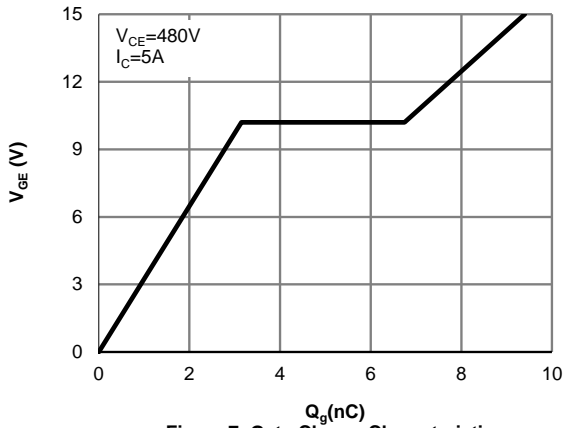


Figure 7: Gate-Charge Characteristics

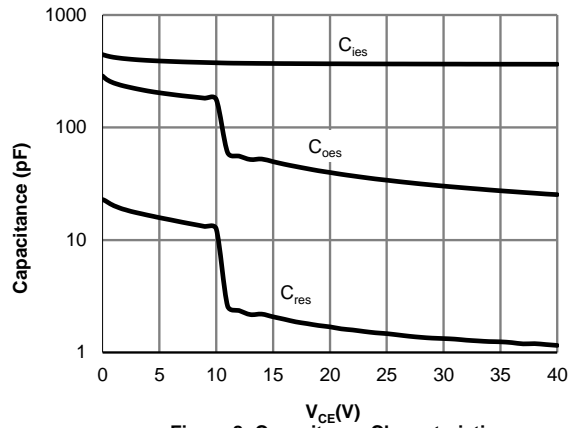


Figure 8: Capacitance Characteristic

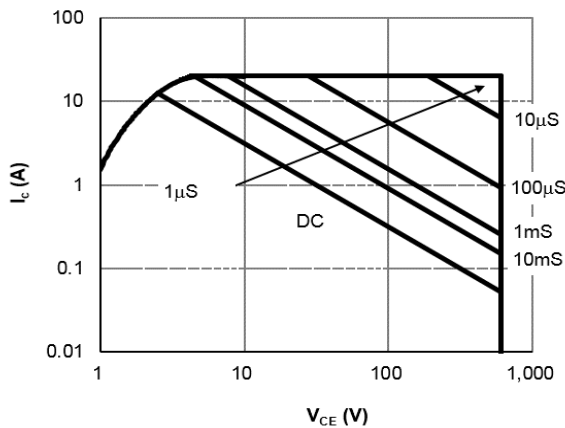


Figure 9: Forward Bias Safe Operating Area
($T_C=25^\circ\text{C}, V_{GE}=15\text{V}$)

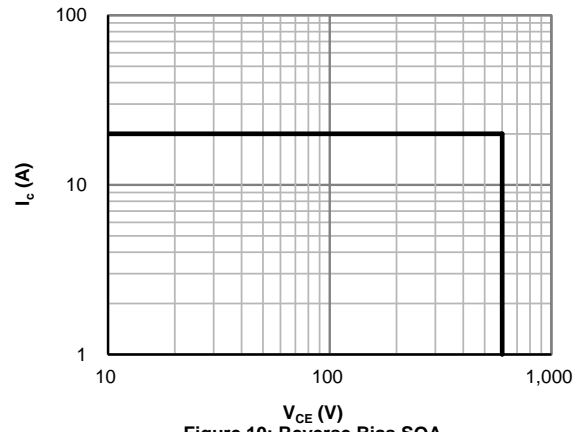


Figure 10: Reverse Bias SOA
($T_J=150^\circ\text{C}, V_{GE}=15\text{V}$)

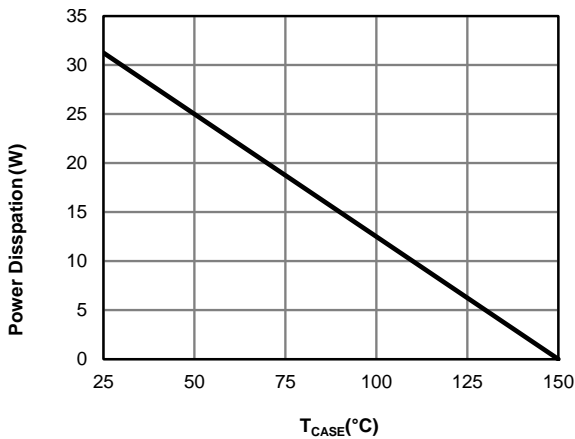


Figure 11: Power Dissipation as a Function of Case

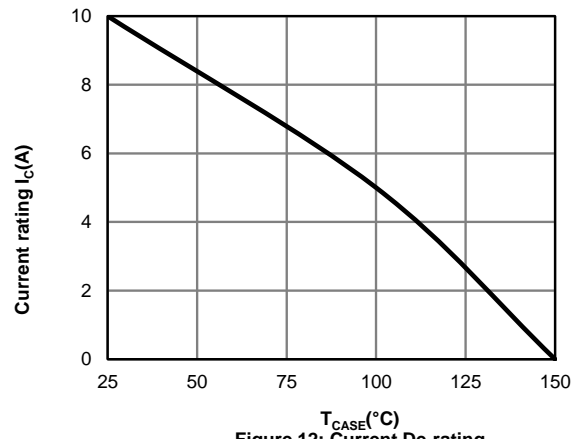


Figure 12: Current De-rating

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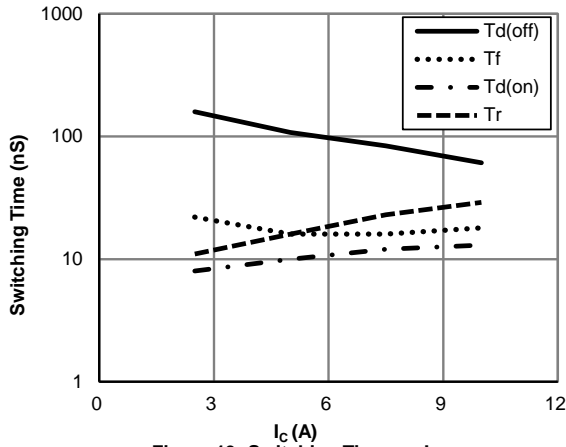


Figure 13: Switching Time vs. I_C
($T_J=150^\circ\text{C}, V_{GE}=15\text{V}, V_{CE}=400\text{V}, R_g=60\Omega$)

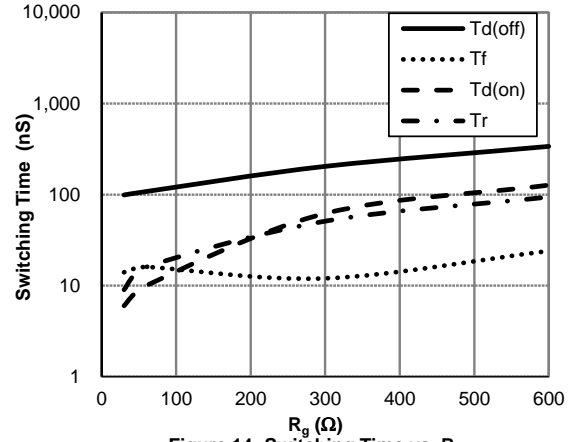


Figure 14: Switching Time vs. R_g
($T_J=150^\circ\text{C}, V_{GE}=15\text{V}, V_{CE}=400\text{V}, I_C=5\text{A}$)

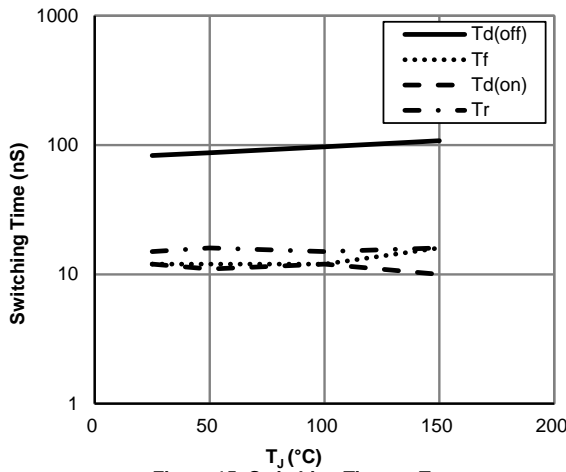


Figure 15: Switching Time vs. T_J
($V_{GE}=15\text{V}, V_{CE}=400\text{V}, I_C=5\text{A}, R_g=60\Omega$)

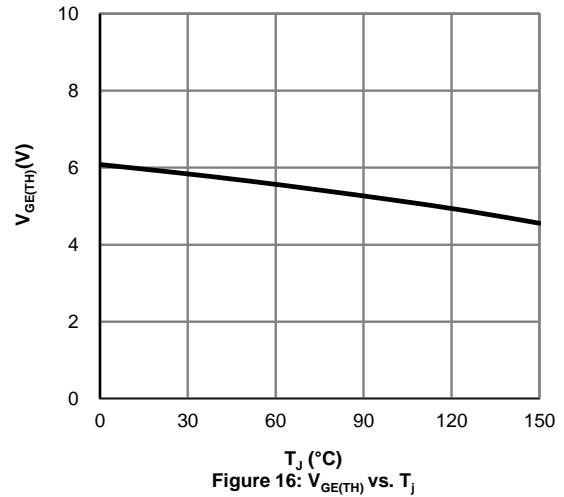


Figure 16: $V_{GE(TH)}$ vs. T_J

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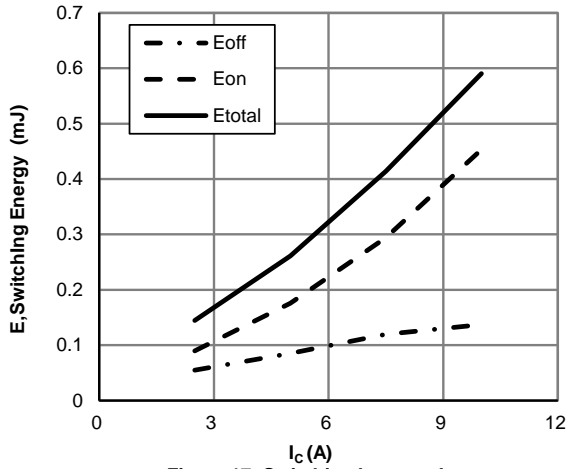


Figure 17: Switching Loss vs. I_C
($T_J=150^\circ\text{C}, V_{GE}=15\text{V}, V_{CE}=400\text{V}, R_g=60\Omega$)

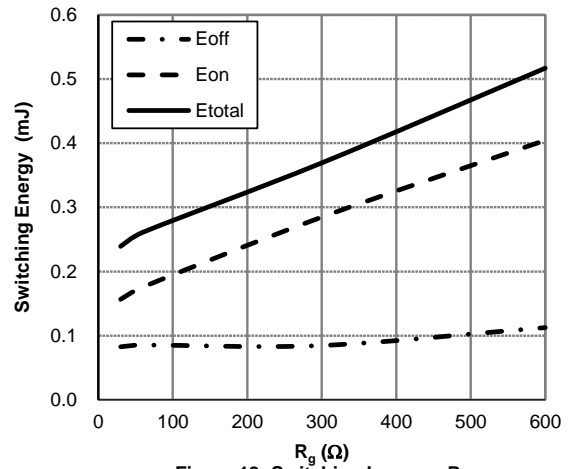


Figure 18: Switching Loss vs. R_g
($T_J=150^\circ\text{C}, V_{GE}=15\text{V}, V_{CE}=400\text{V}, I_C=5\text{A}$)

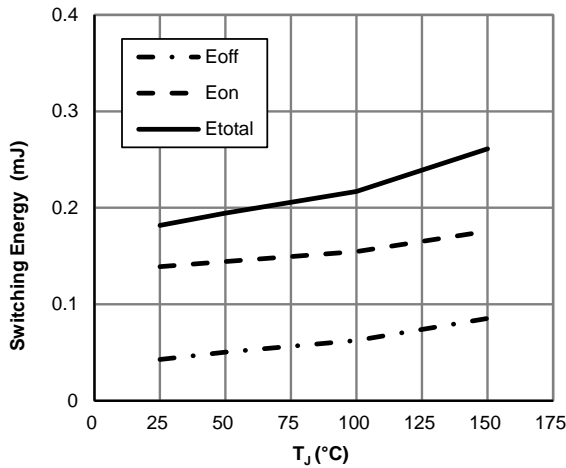


Figure 19: Switching Loss vs. T_J
($V_{GE}=15\text{V}, V_{CE}=400\text{V}, I_C=5\text{A}, R_g=60\Omega$)

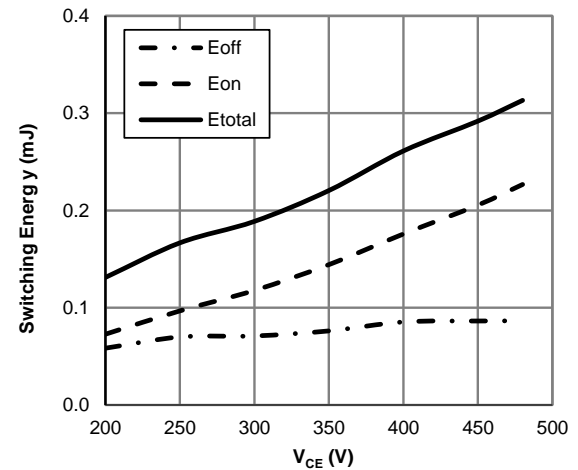


Figure 20: Switching Loss vs. V_{CE}
($T_J=150^\circ\text{C}, V_{GE}=15\text{V}, I_C=5\text{A}, R_g=60\Omega$)

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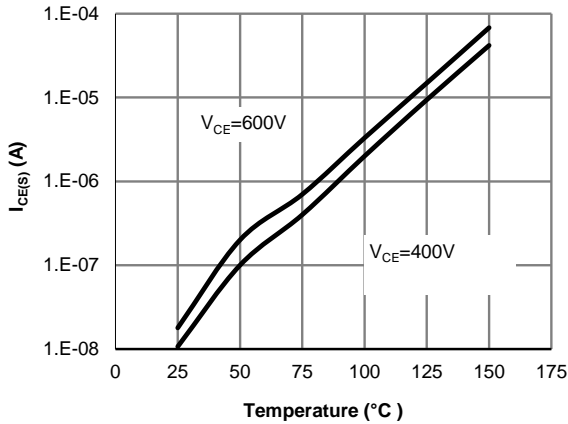


Figure 21: Diode Reverse Leakage Current vs. Junction Temperature

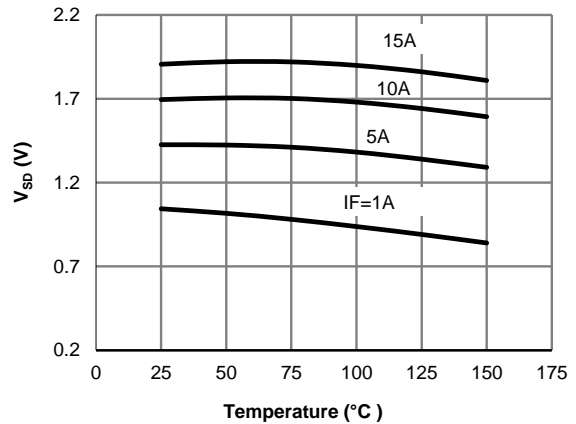


Figure 22: Diode Forward voltage vs. Junction Temperature

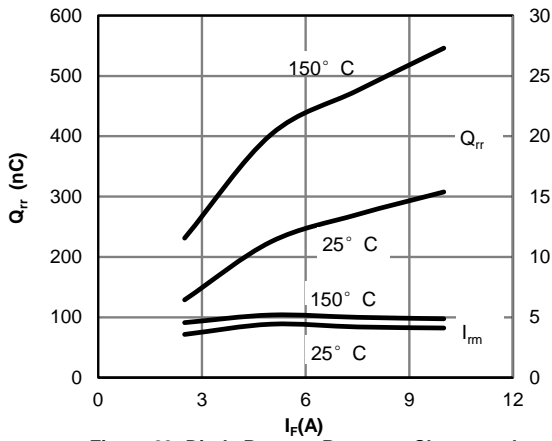


Figure 23: Diode Reverse Recovery Charge and Peak Current vs. Conduction Current
($V_{GE}=15V, V_{CE}=400V, di/dt=200A/\mu s$)

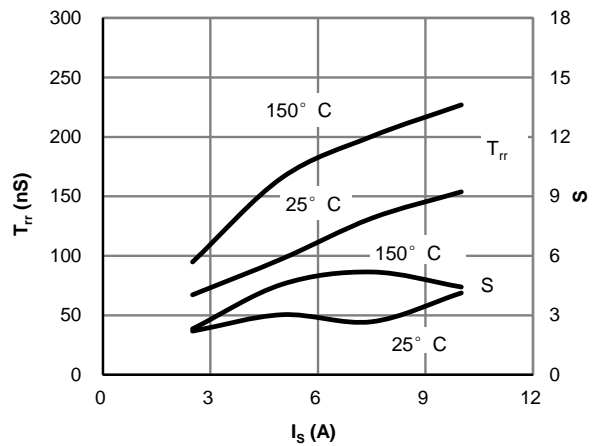


Figure 24: Diode Reverse Recovery Time and Softness Factor vs. Conduction Current
($V_{GE}=15V, V_{CE}=400V, di/dt=200A/\mu s$)

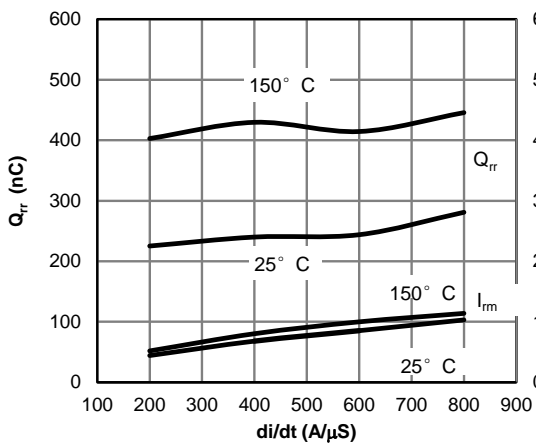


Figure 25: Diode Reverse Recovery Charge and Peak Current vs. di/dt
($V_{GE}=15V, V_{CE}=400V, I_F=5A$)

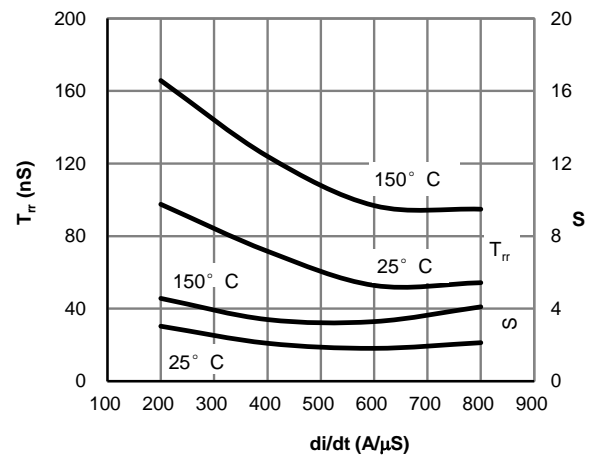


Figure 26: Diode Reverse Recovery Time and Softness Factor vs. di/dt
($V_{GE}=15V, V_{CE}=400V, I_F=5A$)

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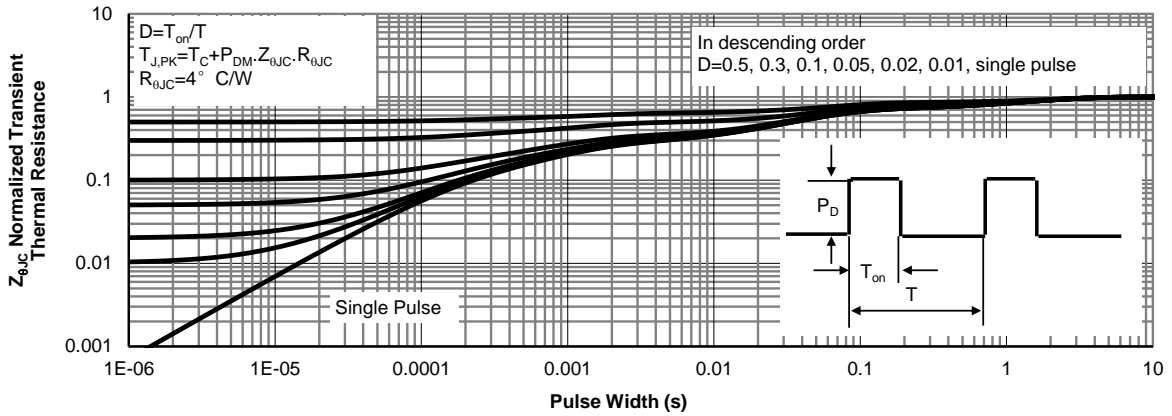


Figure 27: Normalized Maximum Transient Thermal Impedance for IGBT

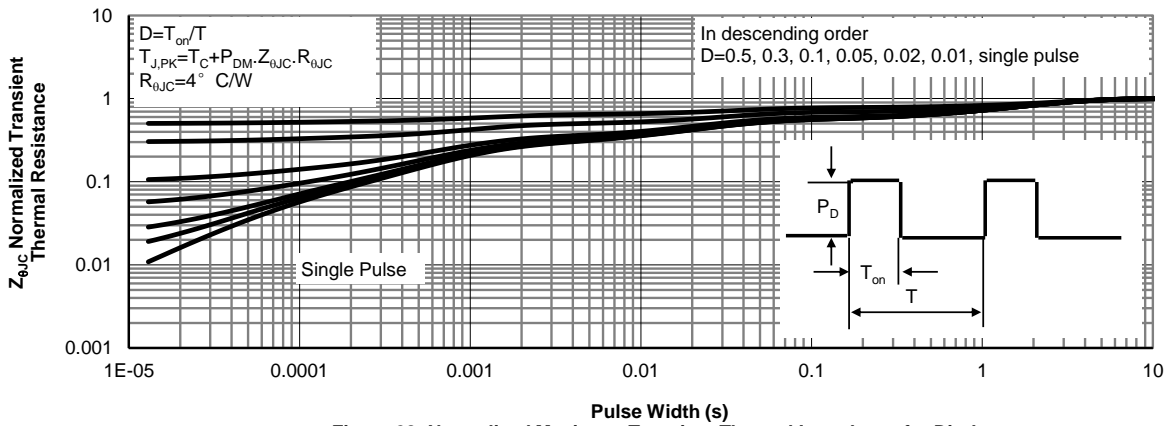
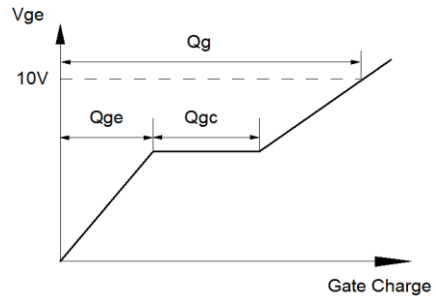
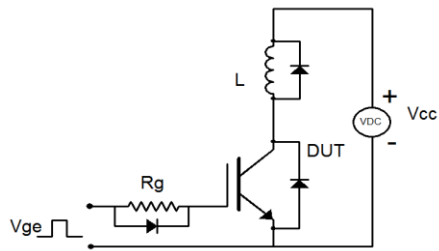
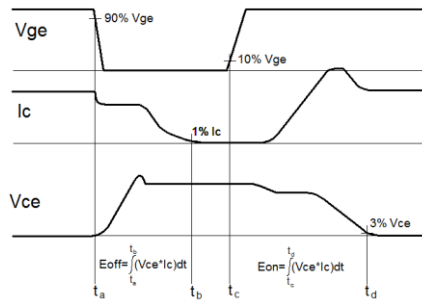
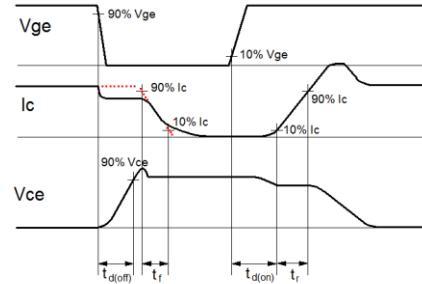
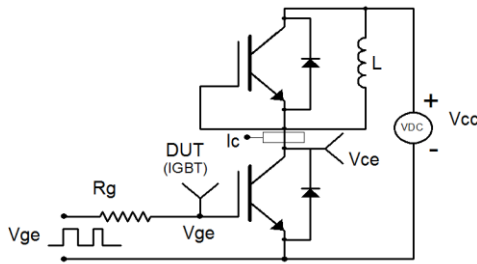


Figure 28: Normalized Maximum Transient Thermal Impedance for Diode

Gate Charge Test Circuit & Waveform



Inductive Switching Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms

